

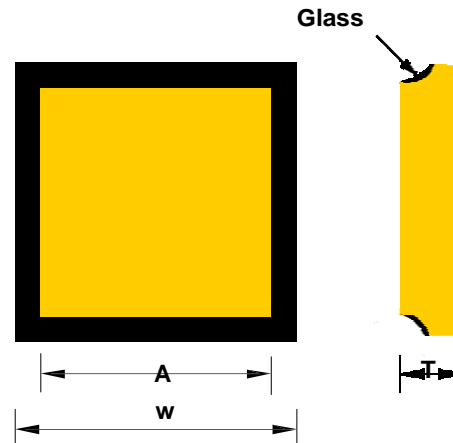


DGS60 THRU DGS70

General Purpose Rectifier GPP Chips

Features

- Fully glass passivated -needs no encapsulation
- Peak reverse voltage to 1800 volts
- Low forward voltage drop(V_F)
- Metallized surface



Description

The GPP chips series are diffused silicon, glass passivated rectifier die.

These devices can be supplied to meet customer's requirements.

The prime application for unencapsulated die is in hybrid circuits. For this reason, a variety of metallized surfaces are available.

Gold is standard for wire bonding, and for soldering application, gold flash chips are supplied.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless specified)

| PARAMETER | SYMBOL | DGS60 | DGS70 | | | | UNIT |
|-------------------------|-----------|-------------|--------|--|--|--|-------|
| Dimension | W | 60±3 | 70±3 | | | | mils |
| Dimension | A | 45±3 | 57±3 | | | | mils |
| Dimension | T | 265±8 | | | | | μm |
| Peak Inverse Voltage | V_B | 1100 | | | | | Volts |
| Forward current | I_F | 1.5~2.0 | 2.0 | | | | Amps |
| Forward Voltage Drop | V_F | ≤0.98 | ≤0.98 | | | | Volts |
| Forward Surge current | I_{FSM} | 50 | 50 | | | | Amps |
| Reverse Recovery Time | T_{RR} | ≥ 1000 | ≥ 1000 | | | | ns |
| Junction Temperature | T_{JFM} | 175 | 175 | | | | °C |
| Reverse Current at 25°C | I_R | 2 | 2 | | | | μA |
| Storage Temperature | T_{ST} | -65 --- 175 | | | | | °C |
| Die attach Temperature | T_d | 375 | | | | | °C |

Note :

Other dimension of GPP chip ranging from 42 mils to 600 mils which is not specified on the list, can also be supplied by special procurement agreement.